CUKUPEAN PATENT UPFICE

Patent Abstracts of Japan

PUBLICATION NUMBER

PUBLICATION DATE

2002076329

15-03-02

APPLICATION DATE

APPLICATION NUMBER

01-09-00

2000265783

(a)

APPLICANT:

NEC CORP;

INVENTOR:

KUZUHARA MASAAKI;

INT.CL.

: H01L 29/778 H01L 21/338 H01L 29/812

H01L 21/205 H01L 29/201

TITLE

SEMICONDUCTOR DEVICE

(b)

MARK MESSAGE

ABSTRACT: PROBLEM TO BE SOLVED: To improve productivity, a heat radiating characteristic and the high speed operability of an element in a group III nitride semiconductor element.

> SOLUTION: An epitaxial growing layer constituted of a group III nitride semiconductor is formed on a sapphire substrate with a face A ((11-20) face) as a main face. Then, a gate electrode 16, a source electrode 15 and a drain electrode 17 are formed on it. The extending directions of the electrodes are arranged to become the angle of within 20° with respect to a sapphire c-axis.

COPYRIGHT: (C)2002,JPO

BEST AVAILABLE COPY